



DMG7408SFG

30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C		
	23mΩ @ V _{GS} = 10V	7.0A		
30V	33mΩ @ V _{GS} = 4.5V	6.0A		

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

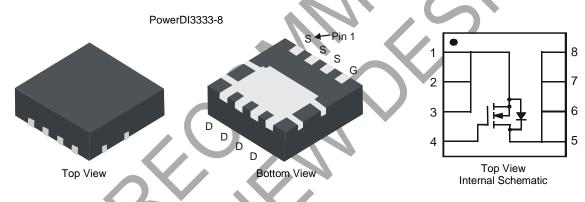
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low RDS(ON) Ensures On State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8
 Enabling Smaller End Product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
DMG7408SFG-7	PowerDI3333-8	2000/Tape & Reel
DMG7408SFG-13	PowerDI3333-8	3000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



G78 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



N34 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit V V		
Drain-Source Voltage Gate-Source Voltage				V _{DSS}	30
				V _{GSS}	±20
	Steady State	T _A = +25°C T _A = +70°C	ID	7.0 5.5	А
Continuous Drain Current (Note 5) $V_{GS} = 10V$	t<10s	T _A = +25°C T _A = +70°C	ID	9.5 7.5	А
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	6.0 5.7	А
	t<10s	T _A = +25°C T _A = +70°C	ID	8.0 6.3	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	66	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	3.0	А
Avalanche Current (Note 7)			IAS	9	А
Avalanche Energy (Note 7)			E _{AS}	12	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)		PD	1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State t<10s	R _θ ja	131 72	°C/W °C/W
Total Power Dissipation (Note 5)	18103	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State t<10s	R _θ JA	63 35	°C/W °C/W
Thermal Resistance, Junction to Case (Note 5)		R _θ JC	7.1	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Cumphel		Turn	Max	11	Test Condition
	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	BV _{DSS}					
Drain-Source Breakdown Voltage		30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	IDSS		-	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	lgss	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.45	2.4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance			15 25	23 33	mΩ	$V_{GS} = 10V, I_D = 10A$
Static Drain-Source On-Resistance	R _{DS(ON)}	-				$V_{GS} = 4.5V, I_D = 7.5A$
Forward Transfer Admittance	Y _{fs}	-	11	-	S	$V_{DS} = 5V, I_{D} = 10A$
Diode Forward Voltage	V _{SD}	-	0.72	1	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	-	478.9	-	pF	
Output Capacitance	Coss	-	96.7	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	61.4	-	pF	
Gate Resistance	Rg	0.4	1.1	1.6	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	5.0	8	nC	
Total Gate Charge (V _{GS} = 10V)	Qg	-	10.5	17	ne)/
Gate-Source Charge	Q _{gs}	-	1.8	-	nC	$V_{\rm DS} = 15 V, I_{\rm D} = 10 A$
Gate-Drain Charge	Q _{gd}	-	1.6	-	nC	
Turn-On Delay Time	t _{D(ON)}	-	2.9	-	ns	
Turn-On Rise Time	t _R	-	7.9	-	ns	$V_{GS} = 10V, V_{DS} = 15V,$
Turn-Off Delay Time	t _{D(OFF)}	-	14.6	-	ns	$R_G = 3\Omega, R_L = 1.5\Omega$
Turn-Off Fall Time	t _F	-	3.1	-	ns	

5. R_{0JA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

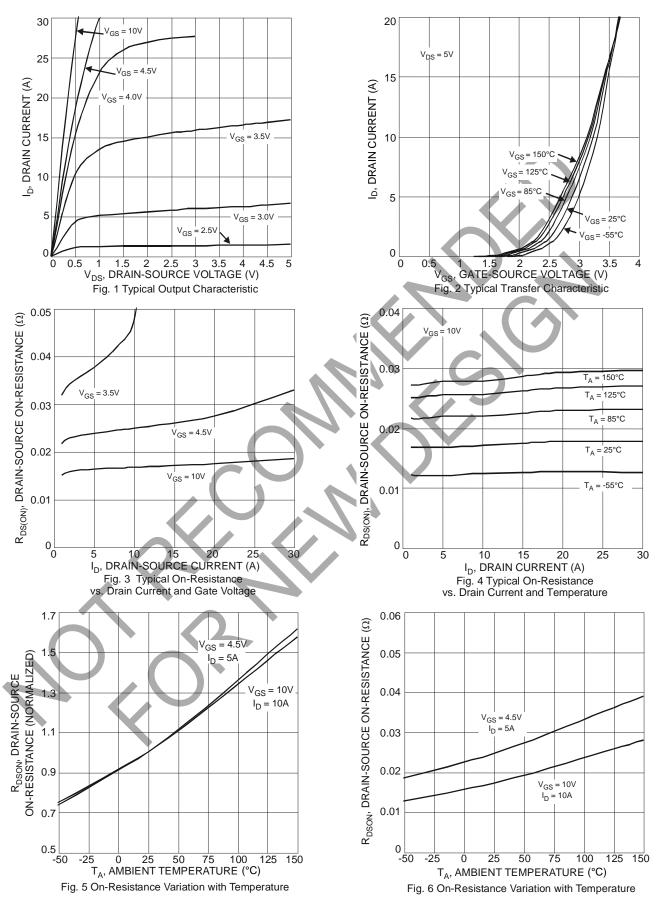
7. UIS in production with L = 0.3mH, T_J = +25°C.

Short duration pulse test used to minize self-heating effect.
 Guaranteed by design. Not subject to product testing.



NOT RECOMMENDED FOR NEW DESIGN USE <u>DMN3025SFV</u>

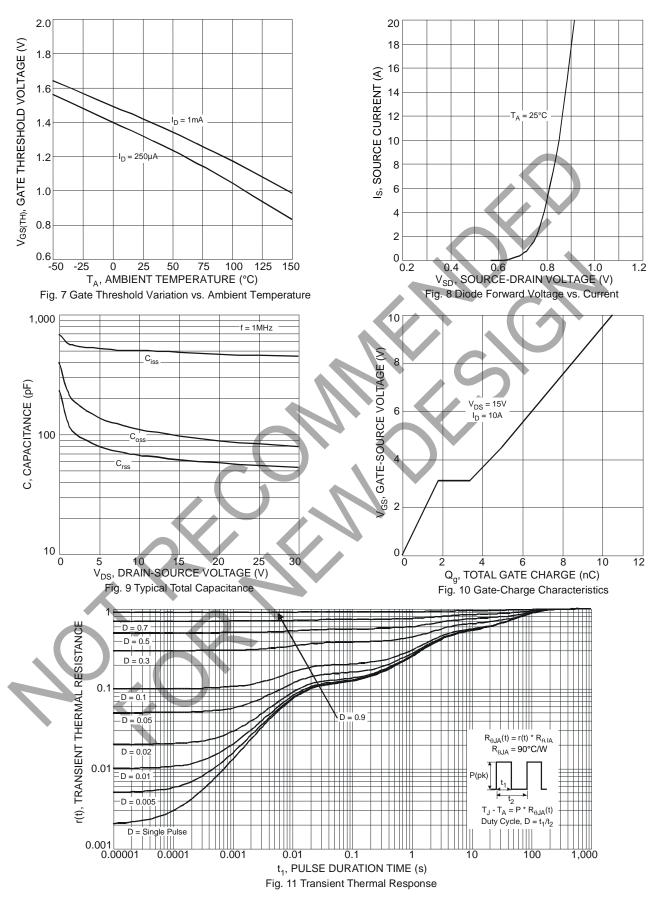
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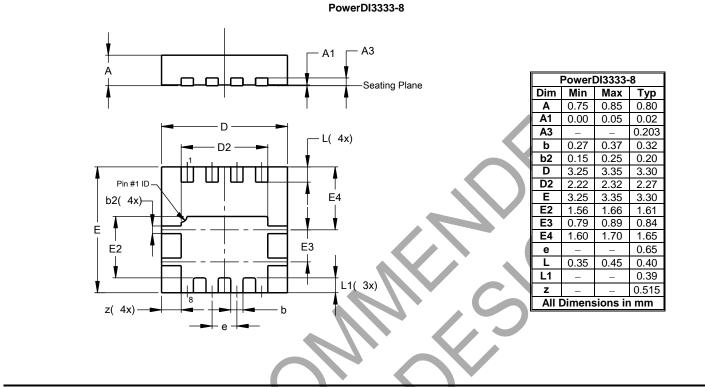
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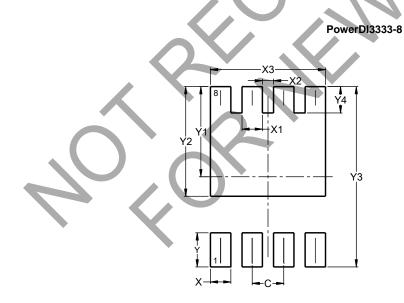
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



Suggested Pad Layout

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Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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